

27. (new) A capacitor construction comprising:

C) a surface area enhancement layer comprising undoped rugged polysilicon over a substrate, the enhancement layer having an outer surface area per unit area that is greater than an inner surface area per unit area of the enhancement layer;

a first capacitor electrode on and in direct contact with the enhancement layer but not comprising the enhancement layer as part of the first electrode, the first electrode having an inner surface area per unit area and an outer surface area per unit area that are both greater than the inner surface area per unit area of the enhancement layer;

a capacitor dielectric layer over the first electrode; and

a second capacitor electrode over the dielectric layer.

28. (new) A capacitor construction comprising:

an opening in an insulative layer over a substrate, the opening having sides and a bottom;

a HSG polysilicon layer over the sides of the opening but not over the bottom;

C' a conformal first capacitor electrode on the HSG polysilicon layer but not comprising the HSG polysilicon layer as part of the first electrode, the first electrode being sufficiently thin that the first electrode has a rugged outer surface with an outer surface area per unit area greater than a surface area per unit area of the sides of the opening over which the HSG polysilicon layer is formed;

a capacitor dielectric layer on the first electrode; and

a second capacitor electrode over the dielectric layer.

29. (new) The construction of claim 28 wherein the first electrode also has an inner surface area per unit area that is greater than the surface area per unit area of the sides of the opening.